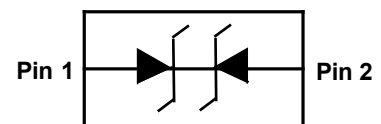


Description

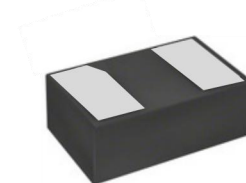
The SXESDUC2XD5VB protects sensitive semiconductor components from damage or upset due to electrostatic discharge (ESD) and other voltage induced transient events. They feature large cross-sectional area junctions for conducting high transient currents, offer desirable electrical characteristics for board level protection, such as fast response time, low operating voltage. It gives designer the flexibility to protect one unidirectional line in applications where arrays are not practical.

Feature

- DFN0603-2L package
- Replacement for MLV(0201)
- Bidirectional configurations
- Response time is typically < 1 ns
- Low clamping voltage
- RoHS compliant
- Transient protection for data lines to
- IEC 61000-4-2(ESD) $\pm 30\text{KV}$ (air), $\pm 30\text{KV}$ (contact);
- IEC 61000-4-4 (EFT) 50A (5/50ns)



DFN0603-2L



Applications

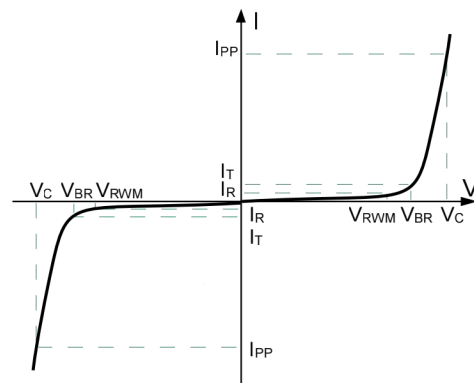
- Cellular phones
- Portable devices
- Digital cameras
- Power supplies

Mechanical Characteristics

- Mounting position: Any
- Qualified max reflow temperature: 260°C
- Device meets MSL 1 requirements
- DFN0603-2L without plating

Electronics Parameter

Symbol	Parameter
V_{RWM}	Peak Reverse Working Voltage
I_R	Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
P_{PP}	Peak Pulse Power
C_J	Junction Capacitance
I_F	Forward Current
V_F	Forward Voltage @ I_F



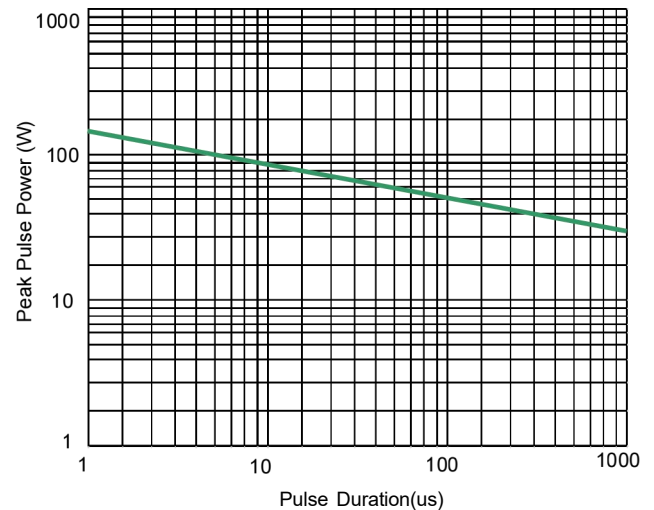
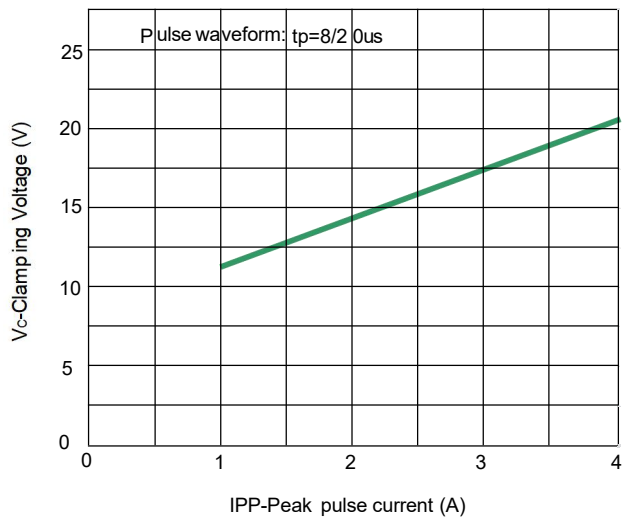
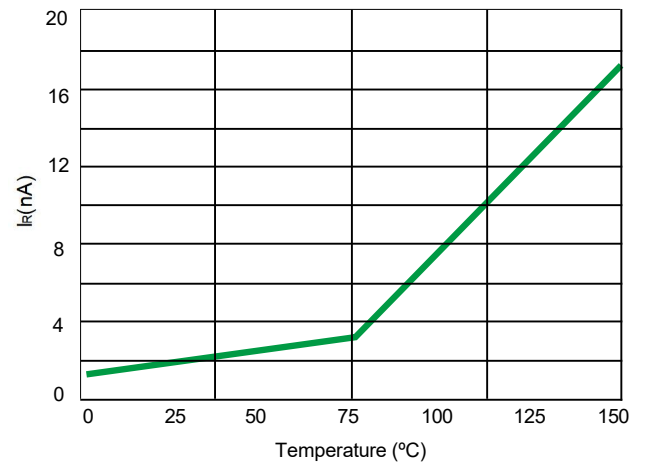
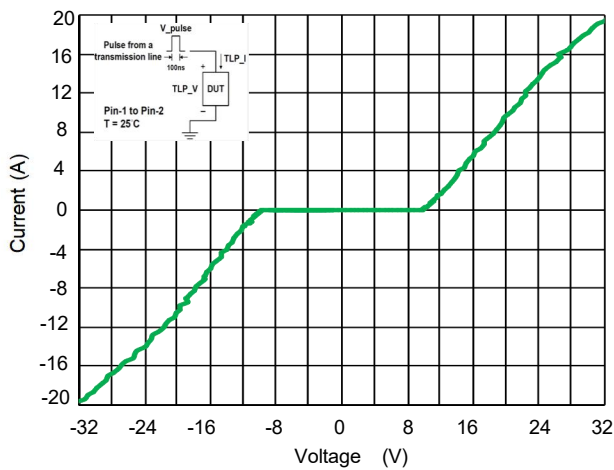
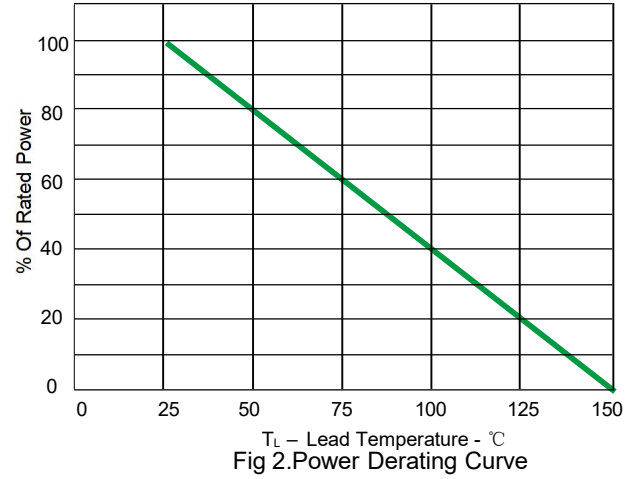
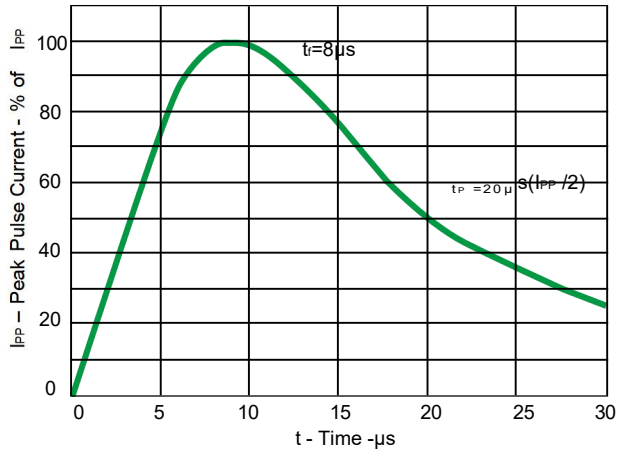
Electrical characteristics per line@25°C(unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Peak Reverse Working Voltage	V_{RWM}				5.0	V
Breakdown Voltage	V_{BR}	$I_T = 1\text{mA}$	5.6		10.5	V
Reverse Leakage Current	I_R	$V_{RWM} = 5\text{V}$ $T=25^\circ\text{C}$			1	μA
Clamping Voltage	V_{CL}	$I_{PP}=16\text{A}$ $t_p=100\text{ns}$		27	29	V
Clamping Voltage	V_C	$I_{PP} = 1\text{A}$ $t_p = 8/20\mu\text{s}$		11	13	V
Clamping Voltage	V_C	$I_{PP} = 4\text{A}$ $t_p = 8/20\mu\text{s}$		21	23	V
Junction Capacitance	C_J	$V_R=0\text{V}$ $f = 1\text{MHz}$		0.3	0.52	pF

Absolute maximum rating@25°C

Rating	Symbol	Value	Units
Peak pulse power($t_p=8/20\mu\text{s}$)	P_{PP}	80	W
Peak pulse current($t_p=8/20\mu\text{s}$)	I_{PP}	4	A
Operating Temperature	T_J	-55 to 150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to 150	$^\circ\text{C}$

Typical Characteristics



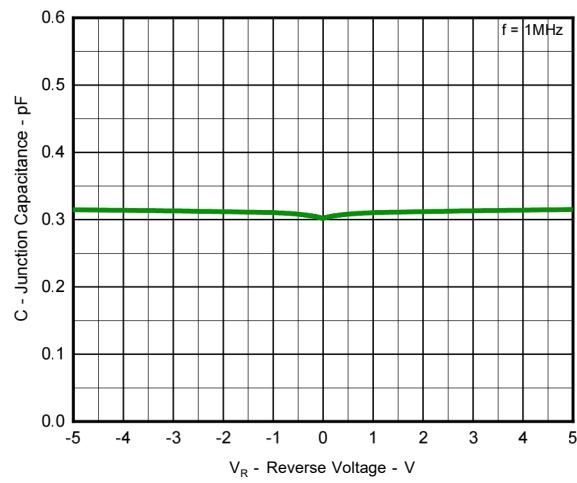


Fig 7. Capacitance vs. Reverse voltage

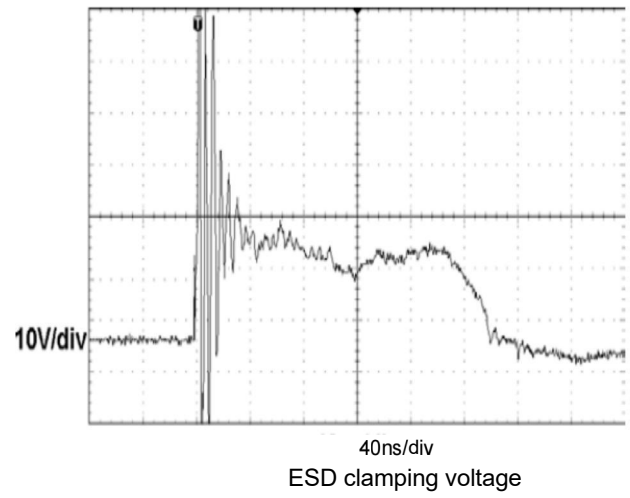


Fig 8. (IEC61000-4-2 +8KV contact)

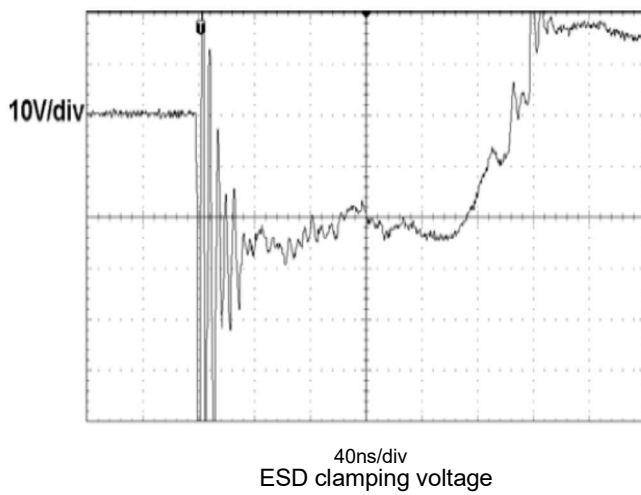
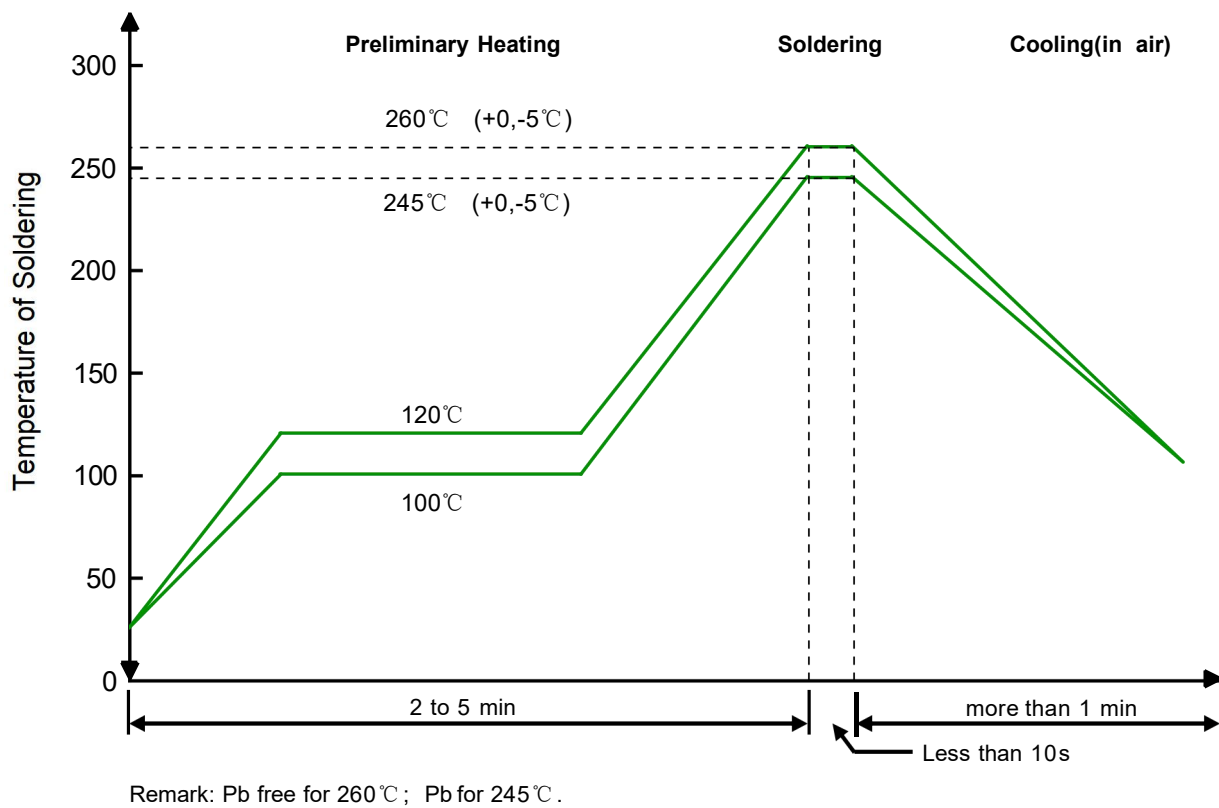


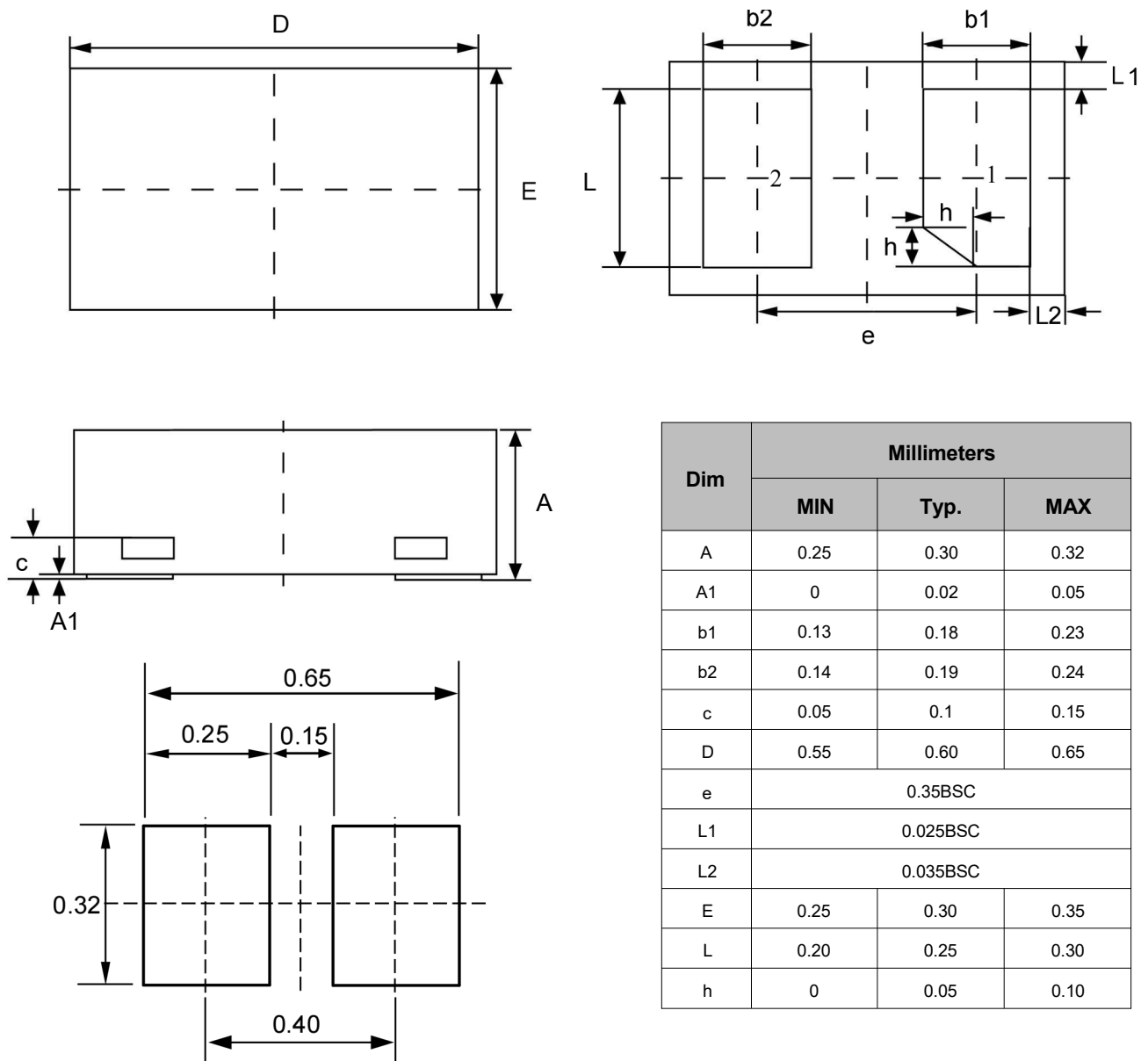
Fig 9. (IEC61000-4-2-8KV contact)

Solder Reflow Recommendation



Ordering information

Device	Package	Reel	Shipping
TAPING	DFN0603-2L (Pb-Free)	7"	12000 / Tape & Reel

Product dimension (DFN0603-2L)


Unit: mm

Suggested PCB Layout